

N-Ch 20V Fast Switching MOSFETS

- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent Cdv/dt effect decline
- ★ Advanced high cell density Trench technology

Product Summary

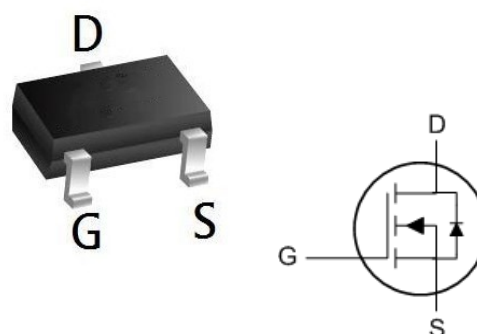


BVDSS	RDSON	ID
20V	21mΩ	5.8A

Description

The SL2300B is the high cell density trenched N-ch MOSFETS, which provides excellent RDSON and efficiency for most of the small power switching and load switch applications. The SL2300B meets the RoHS and Green Product requirement with full function reliability approved.

SOT23-3L Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	20	V
V_{GS}	Gate-Source Voltage	± 12	V
$I_D@T_A=25^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 4.5V ¹	6.0	A
$I_D@T_A=70^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 4.5V ¹	4.0	A
I_{DM}	Pulsed Drain Current ²	15.0	A
$P_D@T_A=25^\circ\text{C}$	Total Power Dissipation ³	1	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	---	125	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	80	$^\circ\text{C/W}$

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	20	---	---	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =4.5V, I _D =3A	---	19	35	mΩ
		V _{GS} =2.5V, I _D =2A	---	35	60	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	0.4	---	1.2	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =16V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =16V, V _{GS} =0V, T _J =55°C	---	---	5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±12V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =5V, I _D =3A	---	10.5	---	S
Q _g	Total Gate Charge (4.5V)	V _{DS} =15V, V _{GS} =4.5V, I _D =3A	---	4.6	---	nC
Q _{gs}	Gate-Source Charge		---	0.7	---	
Q _{gd}	Gate-Drain Charge		---	1.5	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =10V, V _{GS} =4.5V, R _G =3.3Ω I _D =3A	---	1.6	---	ns
T _r	Rise Time		---	42	---	
T _{d(off)}	Turn-Off Delay Time		---	14	---	
T _f	Fall Time		---	7	---	
C _{iss}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1MHz	---	310	---	pF
C _{oss}	Output Capacitance		---	49	---	
C _{rss}	Reverse Transfer Capacitance		---	35	---	

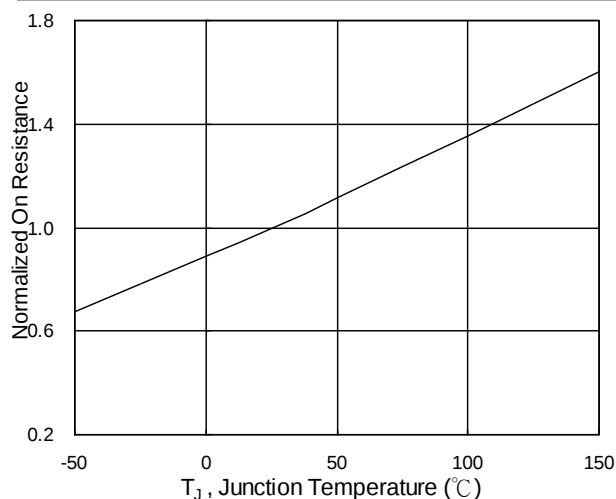
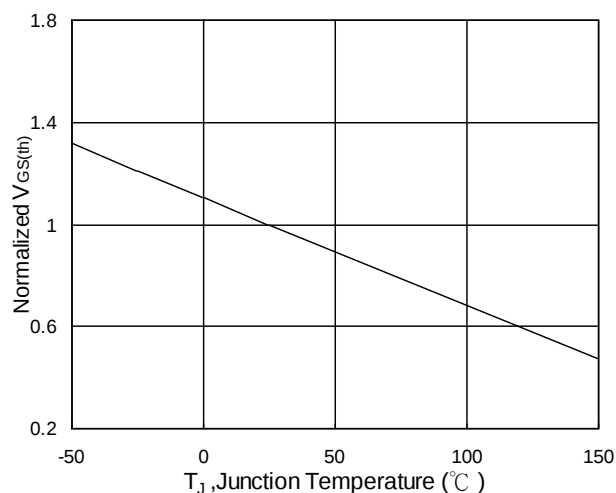
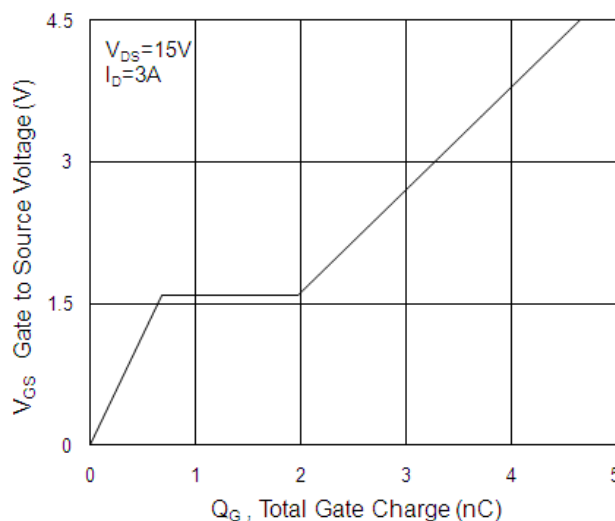
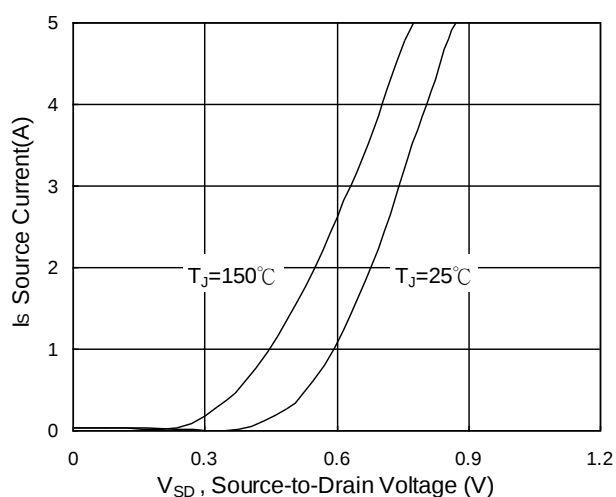
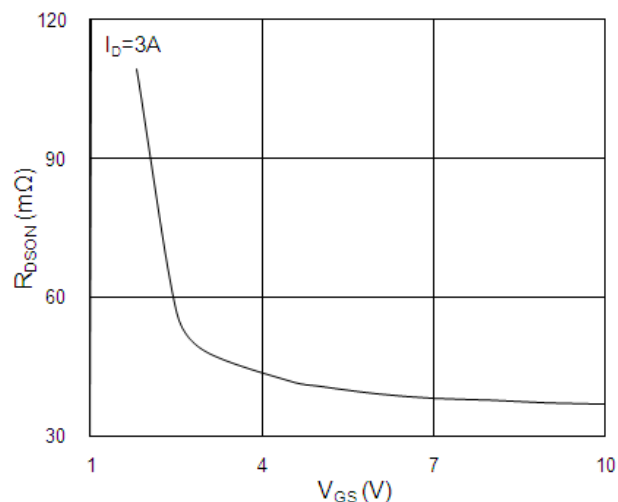
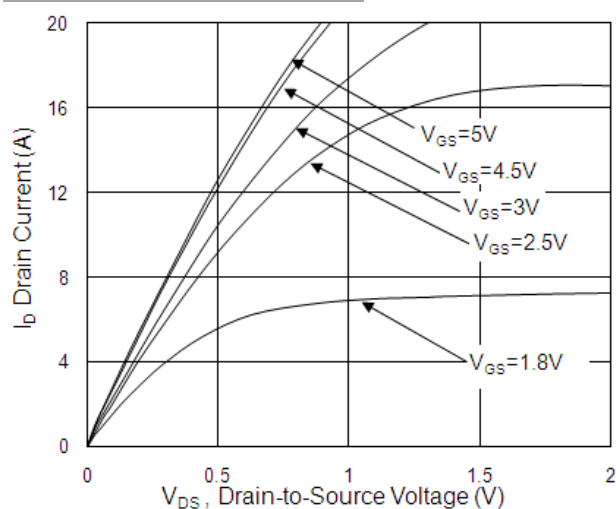
Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current ^{1,4}	V _G =V _D =0V, Force Current	---	---	6.0	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =1A, T _J =25°C	---	---	1.2	V

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The power dissipation is limited by 150°C junction temperature
- 4.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics



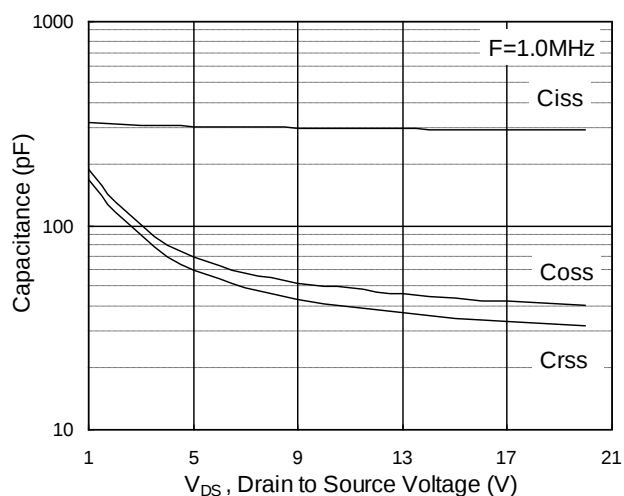


Fig.7 Capacitance

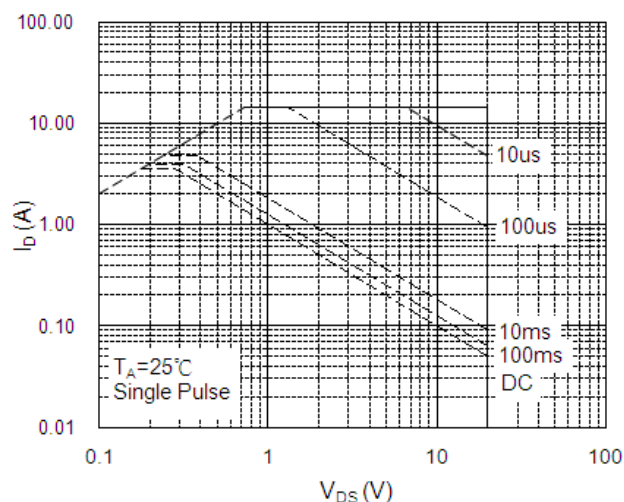


Fig.8 Safe Operating Area

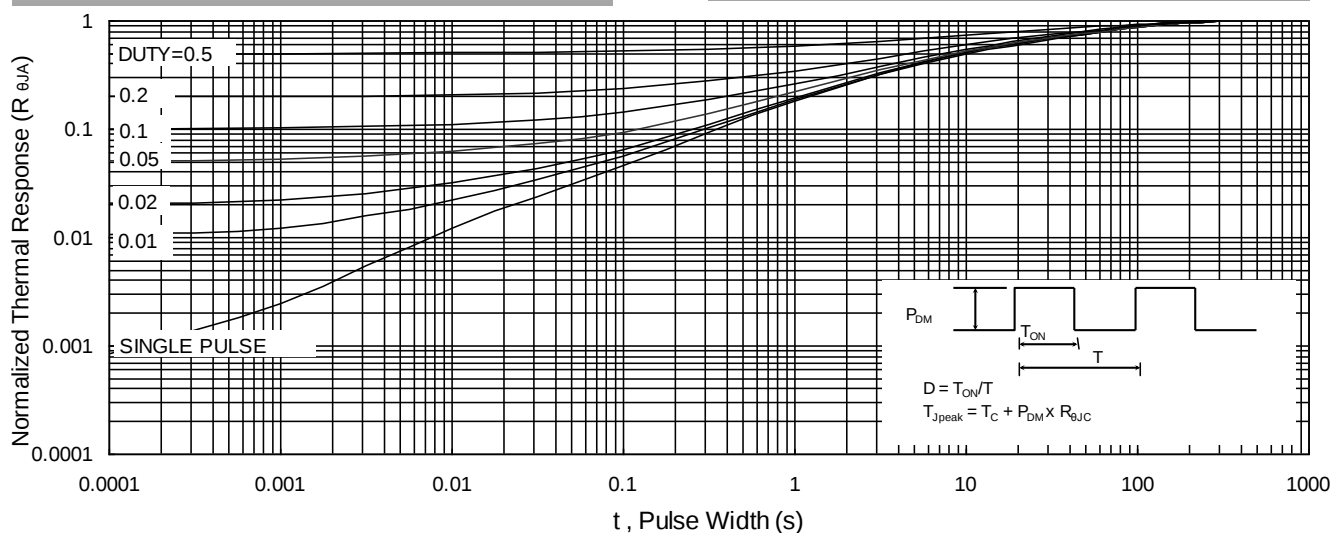


Fig.9 Normalized Maximum Transient Thermal Impedance

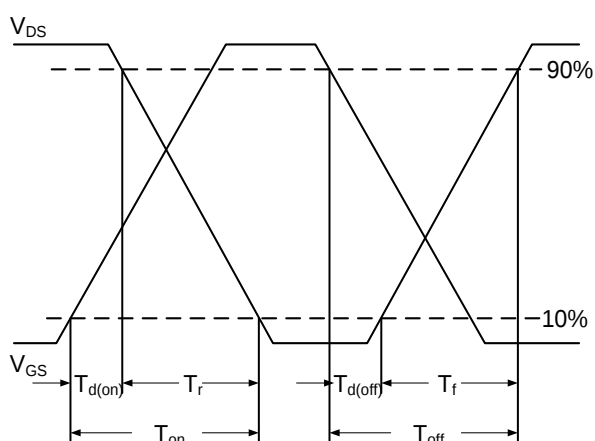


Fig.10 Switching Time Waveform

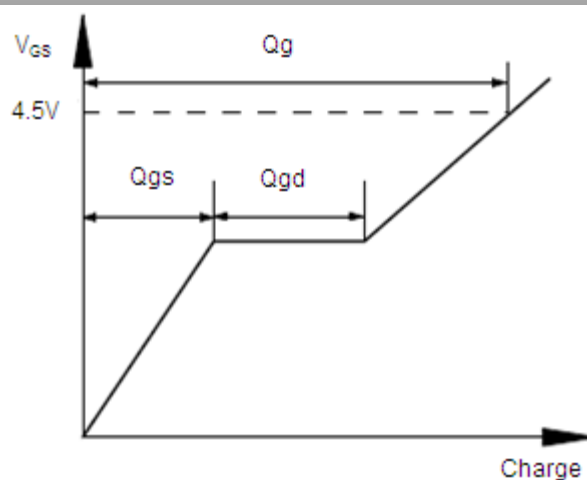
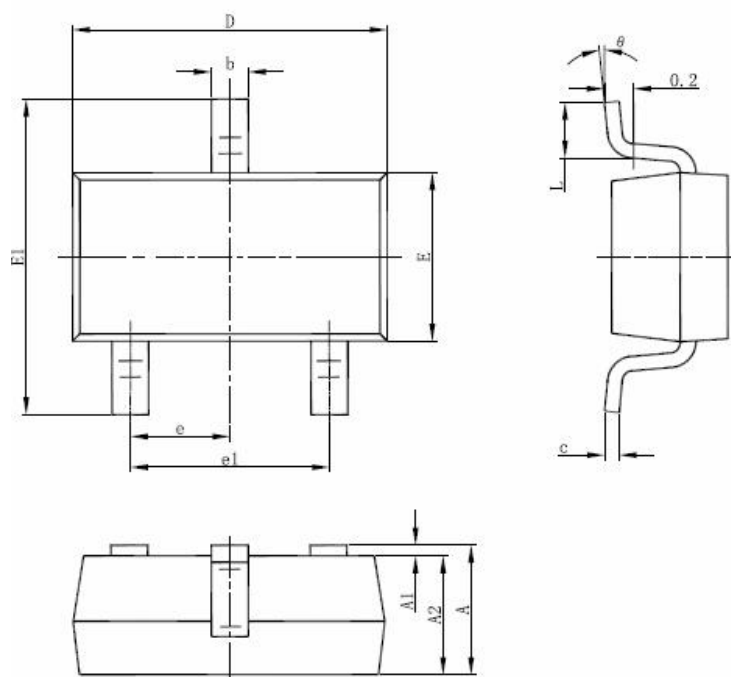


Fig.11 Gate Charge Waveform

Package Mechanical Data-SOT-23-3L



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°